

# SEMiX 202GB066HDs



**SEMiX® 2s**

## Trench IGBT Modules

### SEMiX 202GB066HDs

Preliminary Data

#### Features

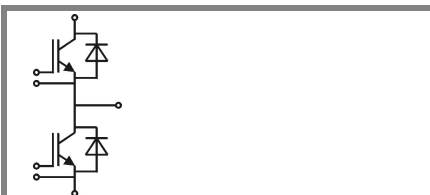
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$  with positive temperature coefficient

#### Typical Applications

- Matrix Converter
- Resonant Inverter
- Current Source Inverter

#### Remarks

- Case temperature limited to  $T_C=125^\circ\text{C}$  max.
- Product reliability results are valid for  $T_j=150^\circ\text{C}$
- use of soft RG necessary
- take care of over-voltage caused by stray inductance



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Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values	Units	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	600	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	275	A
		$T_c = 80^\circ\text{C}$	205	A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	400	A	
$V_{GES}$		$\pm 20$	V	
$t_{psc}$	$V_{CC} = 360\text{ V}; V_{GE} \leq 15\text{ V}; T_j = 150^\circ\text{C}$ $V_{CES} < 600\text{ V}$	6	$\mu\text{s}$	
<b>Inverse Diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	220	A
		$T_c = 80^\circ\text{C}$	160	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	400	A	
$I_{FSM}$	$t_p = 10\text{ ms}; \text{sin.}$	$T_j = 25^\circ\text{C}$	1000	A
<b>Module</b>				
$I_{t(RMS)}$		600	A	
$T_{vj}$		- 40 ... + 175	$^\circ\text{C}$	
$T_{stg}$		- 40 ... + 125	$^\circ\text{C}$	
$V_{isol}$	AC, 1 min.	4000	V	

Characteristics		$T_{case} = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 6,4\text{ mA}$		5,8		V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$			0,1	mA
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0,9	1	V
		$T_j = 150^\circ\text{C}$	0,85	0,9	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	2,75	4,5	m $\Omega$
		$T_j = 150^\circ\text{C}$	4,25	6	m $\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 200\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,45	1,9	V
		$T_j = 150^\circ\text{C}_{chiplev.}$	1,7	2,1	V
$C_{res}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	12,1		nF
$C_{oes}$			0,75		nF
$C_{res}$			0,35		nF
$Q_G$	$V_{GE} = -8 \dots +15\text{V}$		1600		nC
$t_{d(on)}$	$R_{Gon} = 4,2\ \Omega$	$V_{CC} = 300\text{V}$ $I_{Cnom} = 200\text{A}$	65		ns
$t_r$			80		ns
$E_{on}$	$R_{Goff} = 4,2\ \Omega$	$T_j = 150^\circ\text{C}$	6		mJ
$t_{d(off)}$			545		ns
$t_f$			95		ns
$E_{off}$			8		mJ
$R_{th(j-c)}$	per IGBT			0,21	K/W

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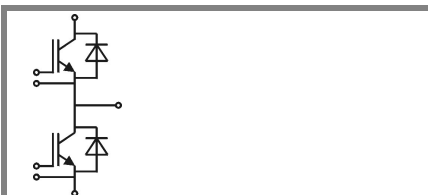
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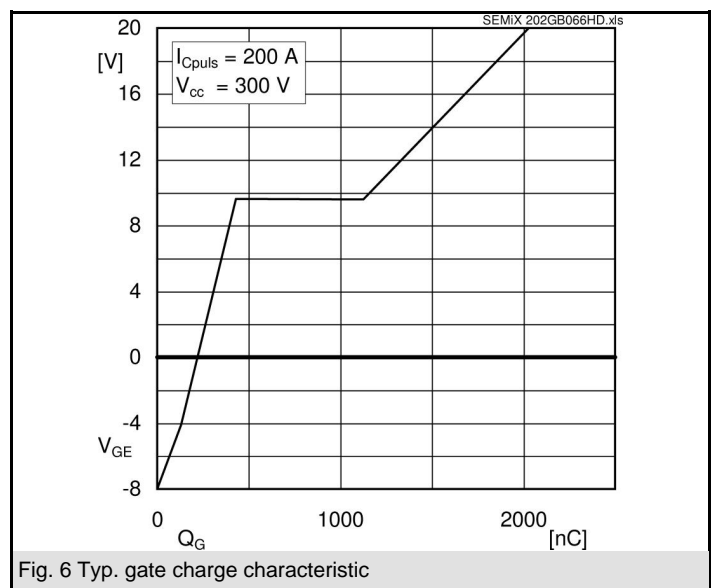
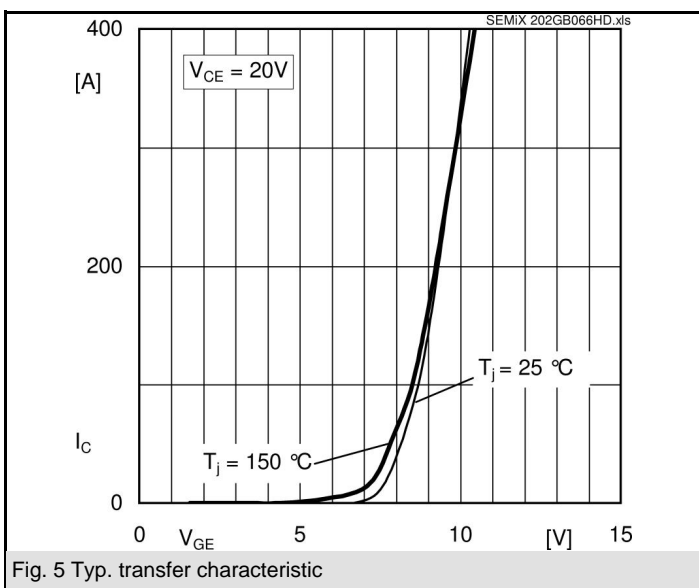
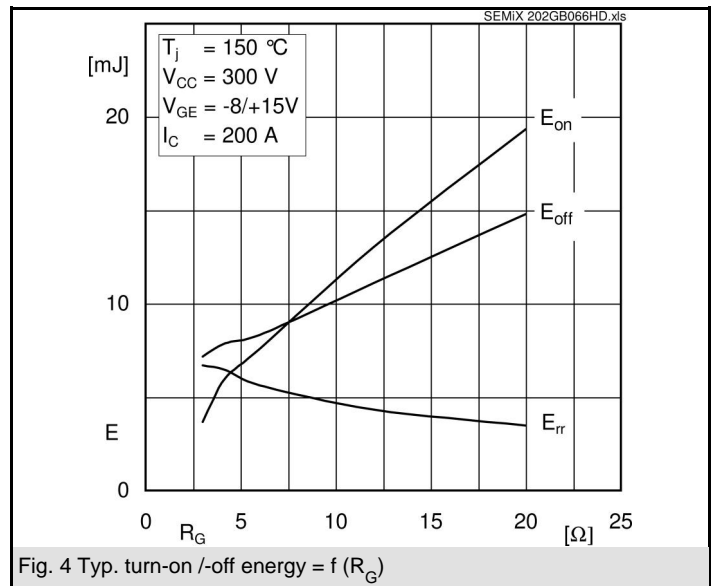
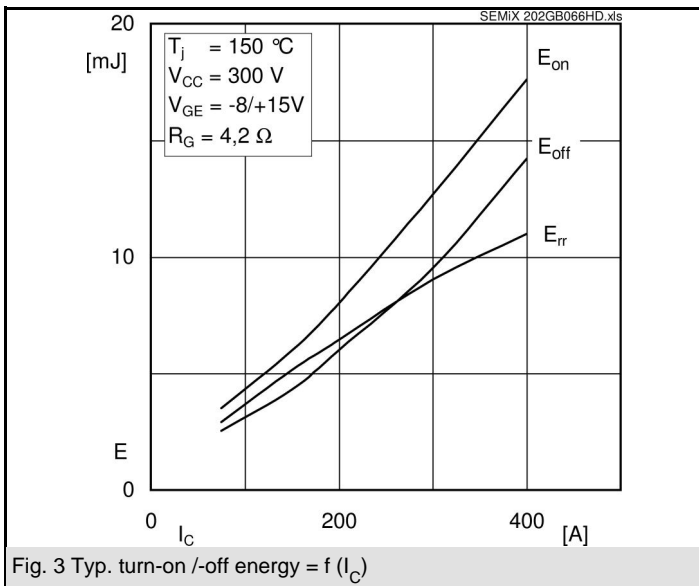
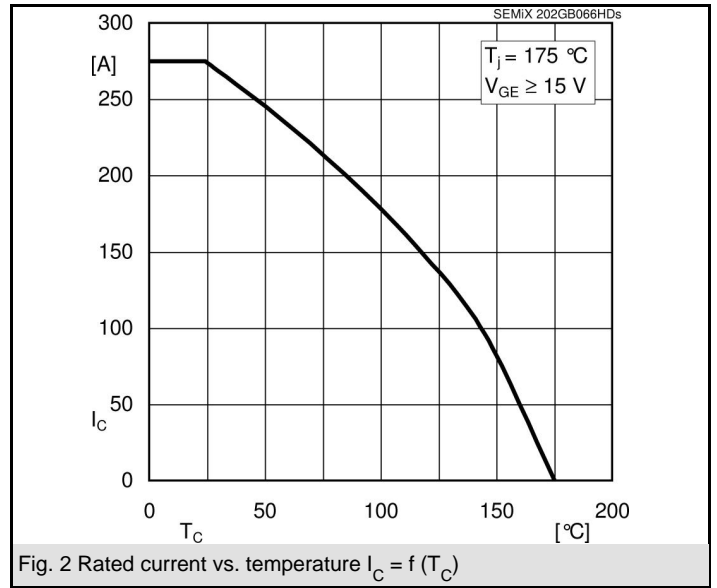
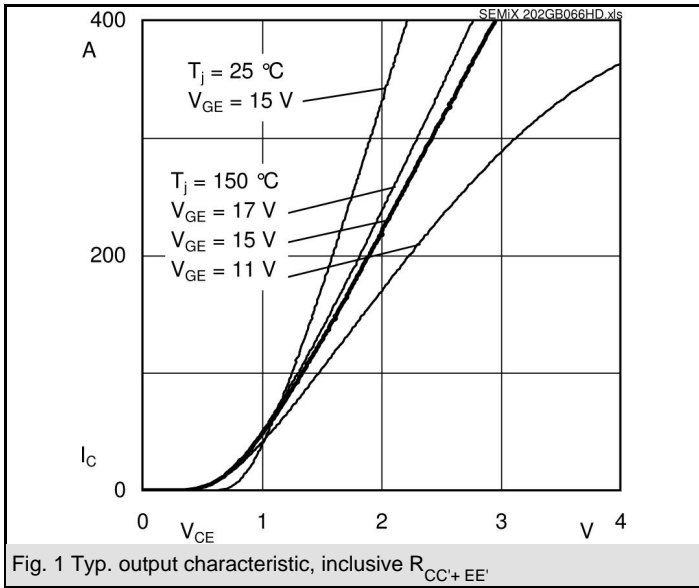


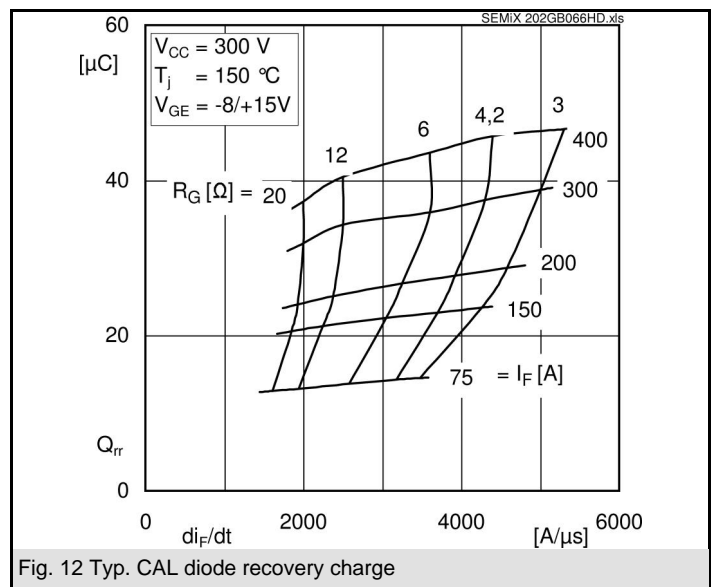
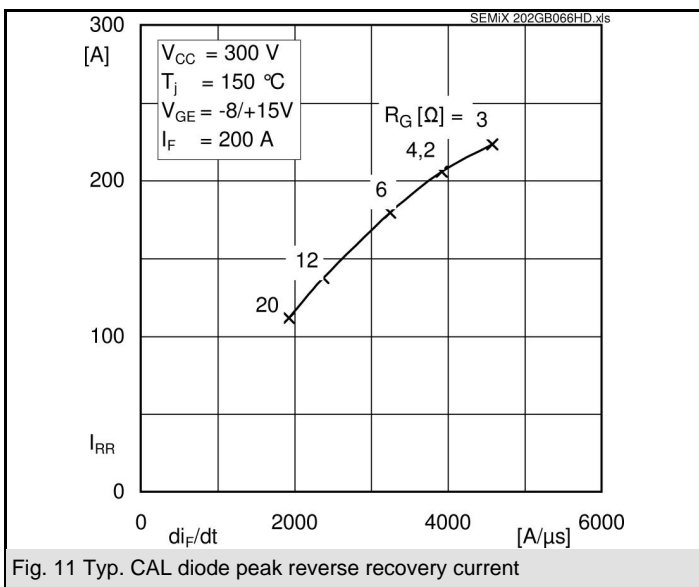
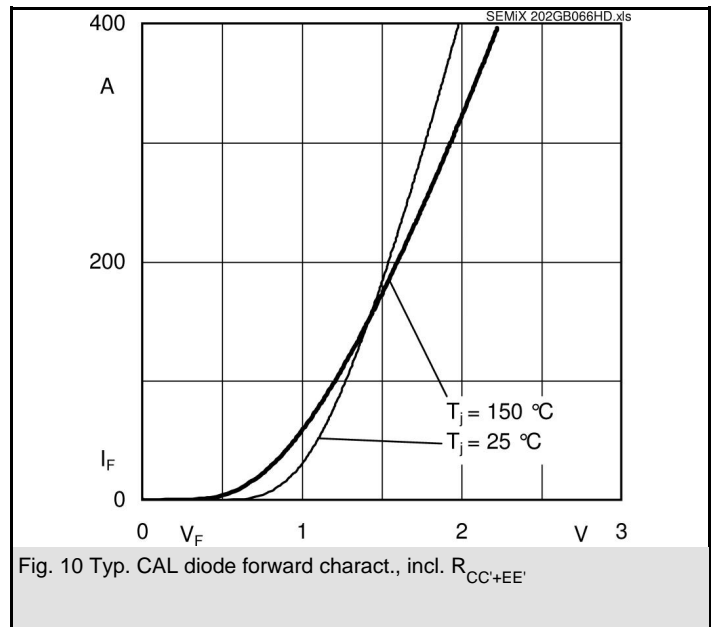
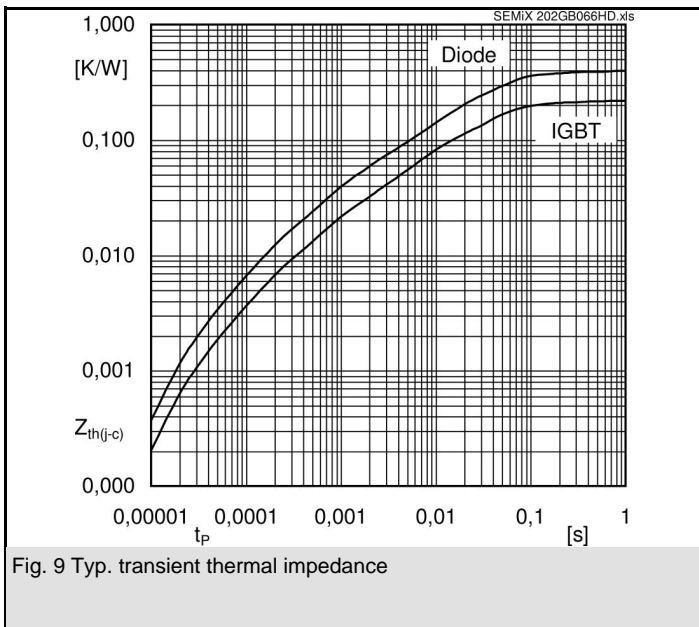
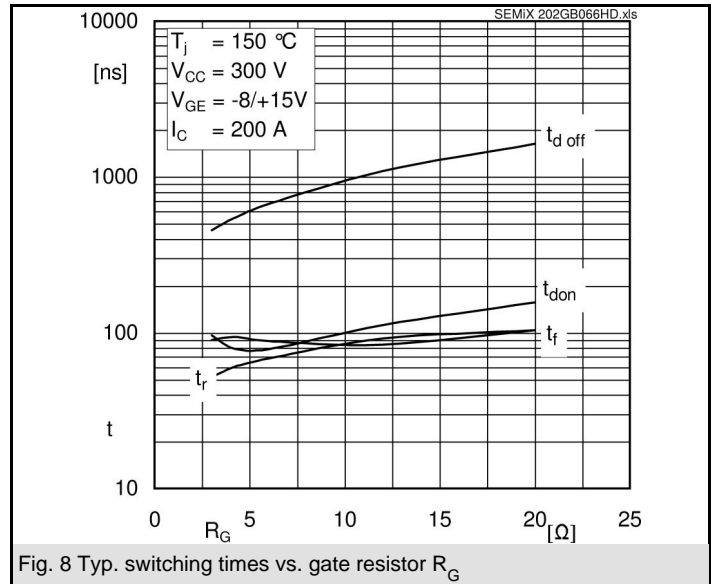
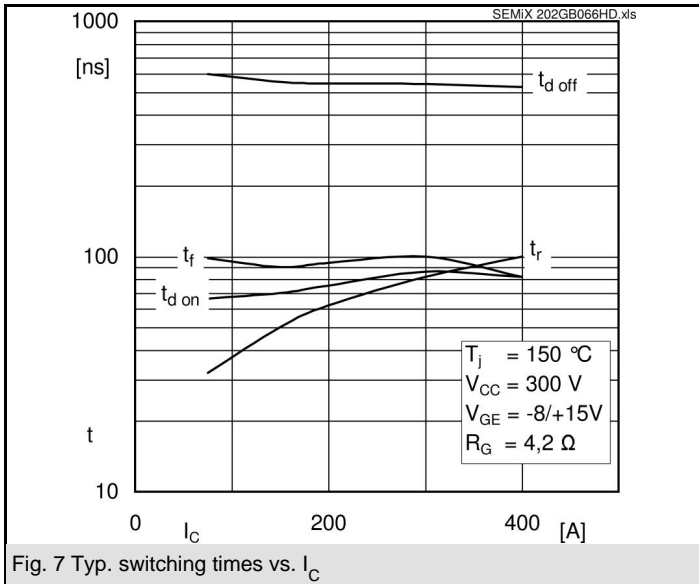
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Characteristics		min.	typ.	max.	Units
<b>Symbol</b>	<b>Conditions</b>				
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 200\text{ A}; V_{GE} = 0\text{ V}$		1,4	1,6	V
					$T_j = 25^\circ\text{C}_{chiplev.}$
			1,4		$T_j = 150^\circ\text{C}_{chiplev.}$
$V_{F0}$			1	1,1	V
					$T_j = 25^\circ\text{C}$
			0,85	0,95	V
					$T_j = 150^\circ\text{C}$
$r_F$			2	2,5	mΩ
					$T_j = 25^\circ\text{C}$
			2,75	3,25	mΩ
					$T_j = 150^\circ\text{C}$
$I_{RRM}$	$I_{Fnom} = 200\text{ A}$		203		A
$Q_{rr}$	$di/dt = 3200\text{ A}/\mu\text{s}$		53		μC
$E_{off}$	$V_{GE} = -8\text{ V}; V_{CC} = 300\text{ V}$		8		mJ
$R_{th(j-c)D}$	per diode			0,4	K/W
<b>Module</b>					
$L_{CE}$			18		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25^\circ\text{C}$	0,7		mΩ
		$T_{case} = 125^\circ\text{C}$	1,05		mΩ
$R_{th(c-s)}$	per module		0,04		K/W
$M_s$	to heat sink (M5)		3	5	Nm
$M_t$	to terminals (M6)		2,5	5	Nm
w			290	250	g
<b>Temperature sensor</b>					
$R_{100}$	$T_c = 100^\circ\text{C}$ ( $R_{25} = 5\text{ k}\Omega$ )		0,493±5%		kΩ
$B_{100/125}$	$R(T) = R_{100} \exp[B_{100/125} (1/T - 1/T_{100})]$ ; $T[\text{K}]; B$		3550±2%		K

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

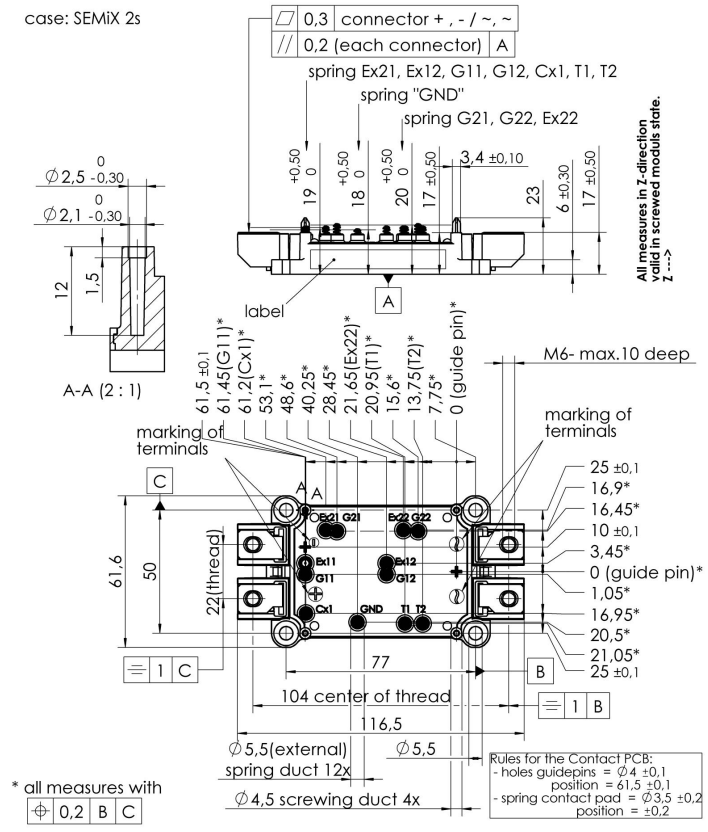




# SEMiX 202GB066HDs

UL Recognized  
File no. E 63 532

Dimensions in mm



Case SEMiX 2s

